

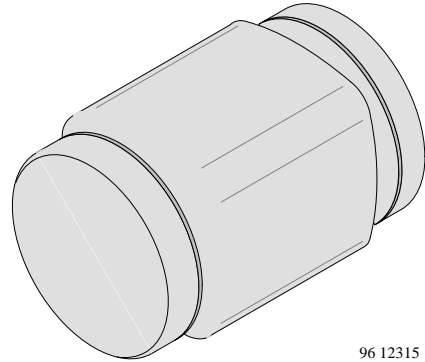
## Silicon Epitaxial Planar Diode

### Features

- Electrical data identical with the device 1N4154
- Micro Melf package

### Applications

Extreme fast switches



96 12315

### Absolute Maximum Ratings

$T_j = 25^\circ\text{C}$

| Parameter                       | Test Conditions      | Type | Symbol    | Value      | Unit             |
|---------------------------------|----------------------|------|-----------|------------|------------------|
| Repetitive peak reverse voltage |                      |      | $V_{RRM}$ | 35         | V                |
| Reverse voltage                 |                      |      | $V_R$     | 25         | V                |
| Peak forward surge current      | $t_p = 1\mu\text{s}$ |      | $I_{FSM}$ | 2          | A                |
| Repetitive peak forward current |                      |      | $I_{FRM}$ | 450        | mA               |
| Forward current                 |                      |      | $I_F$     | 200        | mA               |
| Average forward current         | $V_R = 0$            |      | $I_{FAV}$ | 150        | mA               |
| Power dissipation               |                      |      | $P_V$     | 500        | mW               |
| Junction temperature            |                      |      | $T_j$     | 175        | $^\circ\text{C}$ |
| Storage temperature range       |                      |      | $T_{stg}$ | -65...+175 | $^\circ\text{C}$ |

### Maximum Thermal Resistance

$T_j = 25^\circ\text{C}$

| Parameter        | Test Conditions  | Symbol     | Value | Unit |
|------------------|--|------------|-------|------|
| Junction ambient | mounted on epoxy-glass hard issue, Fig. 1, 35 $\mu\text{m}$ copper clad, 0.9 mm <sup>2</sup> copper area per electrode | $R_{thJA}$ | 500   | K/W  |

## Characteristics

$T_j = 25^\circ\text{C}$

| Parameter             | Test Conditions  | Type | Symbol     | Min | Typ | Max | Unit          |
|-----------------------|--|------|------------|-----|-----|-----|---------------|
| Forward voltage       | $I_F=30\text{mA}$  |      | $V_F$      |     |     | 1   | V             |
| Reverse current       | $V_R=25\text{V}$   |      | $I_R$      |     |     | 100 | nA            |
|                       | $V_R=25\text{V}, T_j=150^\circ\text{C}$                                  |      | $I_R$      |     |     | 100 | $\mu\text{A}$ |
| Breakdown voltage     | $I_R=5\mu\text{A}, t_p/T=0.01,$<br>$t_p=0.3\text{ms}$                    |      | $V_{(BR)}$ | 35  |     |     | V             |
| Diode capacitance     | $V_R=0, f=1\text{MHz},$<br>$V_{HF}=50\text{mV}$                          |      | $C_D$      |     |     | 4   | pF            |
| Reverse recovery time | $I_F=I_R=10\text{mA}, i_R=1\text{mA}$                                    |      | $t_{rr}$   |     |     | 4   | ns            |
|                       | $I_F=10\text{mA}, V_R=6\text{V},$<br>$i_R=0.1 \times I_R, R_L=100\Omega$ |      | $t_{rr}$   |     |     | 2   | ns            |

## Typical Characteristics ( $T_j = 25^\circ\text{C}$ unless otherwise specified)

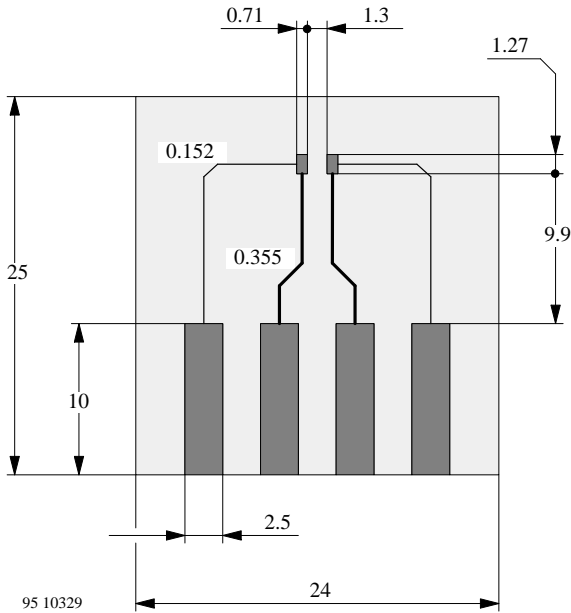


Figure 1. Board for  $R_{thJA}$  definition (in mm)

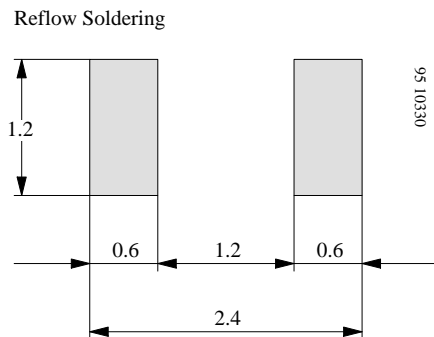


Figure 2. Recommended foot pads (in mm)

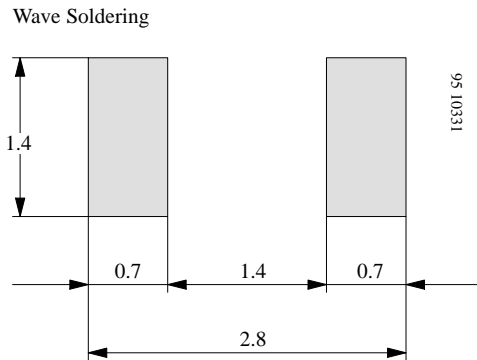


Figure 3. Recommended foot pads (in mm)

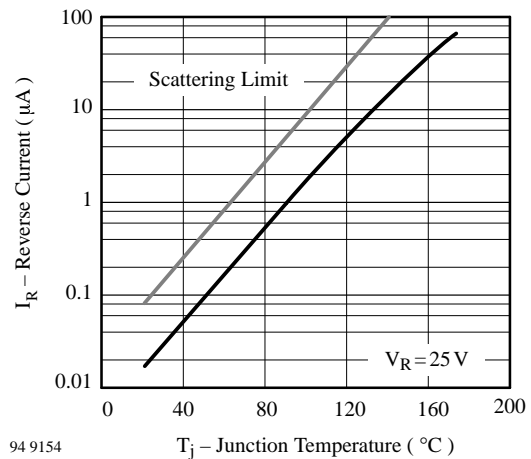


Figure 4. Reverse Current vs. Junction Temperature

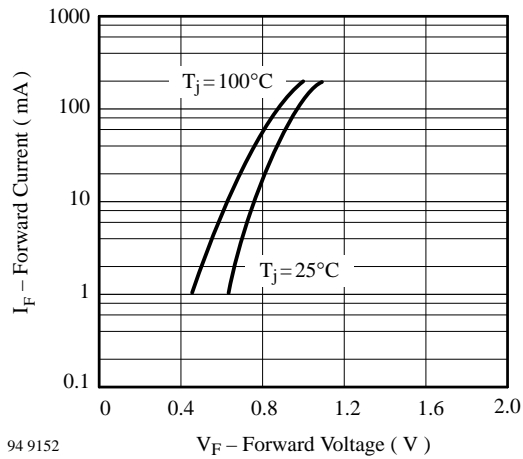


Figure 5. Forward Current vs. Forward Voltage

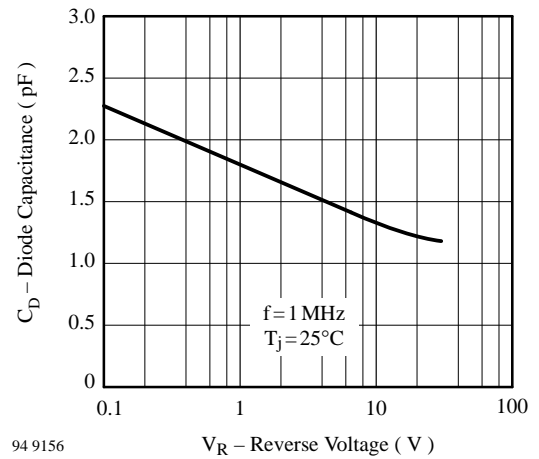
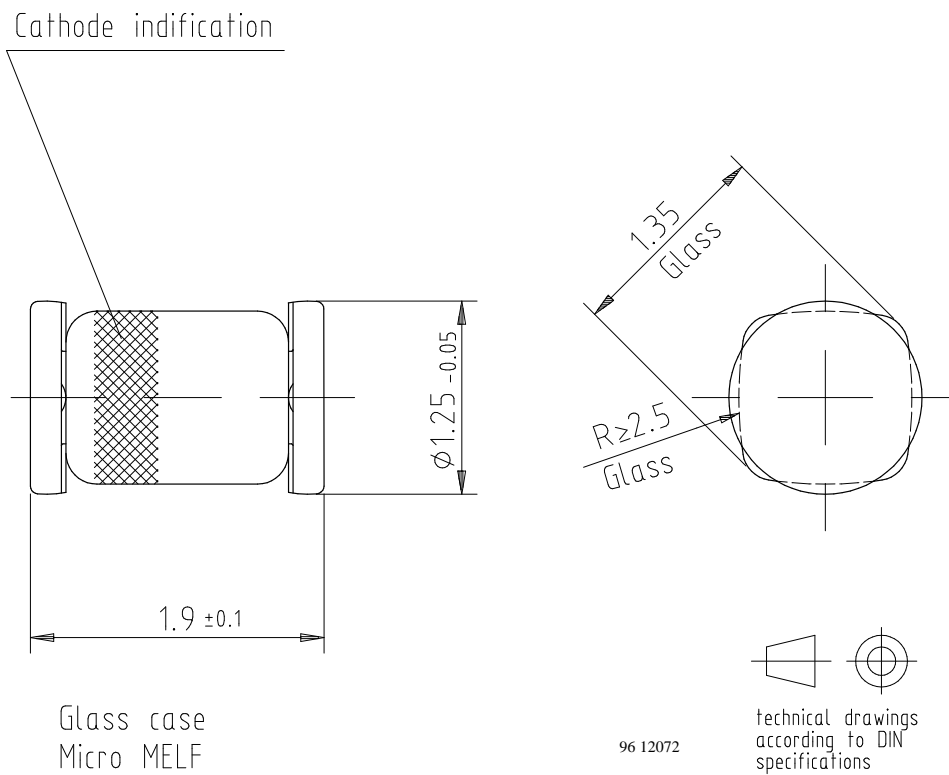


Figure 6. Diode Capacitance vs. Reverse Voltage

**Dimensions in mm**



## Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

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